



IOFFE PHYSICAL-TECHNICAL INSTITUTE

Nanostructures as the Instrument for Materialization of the Problems from the Textbook on Quantum Mechanics

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with

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Presentation consists of two Sections:

1. Coulomb States in Nanostructures, Accidental Degeneracy, and the Laplace-Runge-Lenz Operator

2. Electron in Periodic Potential under Action of Constant Electric Field and Bloch Oscillations

Section 1

Coulomb States in Nanostructures, Accidental Degeneracy, and the Laplace- Runge-Lenz Operator

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- ❖ Introduction: Accidental Degeneracy for Coulomb potential and harmonic oscillator potential
- ❖ How to get transition between two of these cases using Quantum Well nanostructure
- ❖ Looking after the transition
- ❖ Conclusions to the Section

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3D Hydrogen Atom

$$\hat{H} = -\frac{1}{r^2} \frac{\partial}{\partial r} \left(r^2 \frac{\partial}{\partial r} \right) - \frac{1}{r^2 \sin \theta} \frac{\partial}{\partial \theta} \left(\sin \theta \frac{\partial}{\partial \theta} \right) - \frac{1}{r^2 \sin^2 \theta} \frac{\partial^2}{\partial \varphi^2} - \frac{2}{r}$$

$$\Psi = \text{Const} \cdot \left(\frac{2r}{n} \right)^l \exp\left(-\frac{r}{n}\right) Y_{lm}(\theta, \varphi) L_{n+l}^{2l+1} \left(\frac{2r}{n} \right) \quad Ry = \frac{m_e e^4}{2\varepsilon^2 \hbar^2}$$

$$E_n = -\frac{1}{(n+1)^2}, \quad n = 0, 1, \dots \quad a_B = \frac{\hbar^2 \varepsilon}{m_e e^2}$$

Degeneracy of the State with Main Quantum Number n :

$$l = 0, 1, \dots, n, \quad m = -l, -l+1, \dots, 0, \dots, l-1, l \quad \text{Total: } (n+1)^2$$

Accidental degeneracy

Laplace – Runge –Lentz Operator:

$$\hat{\mathbf{A}} = (\hat{\mathbf{p}} \times \hat{\mathbf{L}} - \hat{\mathbf{L}} \times \hat{\mathbf{p}}) - \frac{2}{r} \mathbf{r}$$

$\mathbf{A} = \mathbf{p} \times \mathbf{L} - \frac{2}{r} \mathbf{r}$ - in classical mechanics – constant of motion

$$[\hat{A}_i, \hat{A}_k] = -2ie_{ikl} \hat{H} \hat{L}_l \quad [\hat{L}_i, \hat{A}_k] = ie_{ikl} \hat{A}_l$$

3D ISOTROPIC HARMONIC OSCILLATOR

$$\hat{H} = -\frac{1}{r^2} \frac{\partial}{\partial r} \left(r^2 \frac{\partial}{\partial r} \right) - \frac{1}{r^2 \sin \theta} \frac{\partial}{\partial \theta} \left(\sin \theta \frac{\partial}{\partial \theta} \right) - \frac{1}{r^2 \sin^2 \theta} \frac{\partial^2}{\partial \varphi^2} + Kr^2$$

$$\Psi = \text{Const} \cdot r^l \exp\left(-\frac{\sqrt{K}r^2}{2}\right) Y_{lm}(\theta, \varphi) F\left(-\frac{n-l}{2}, l + \frac{3}{2}, \sqrt{K}r^2\right)$$

$$E_n = 2\sqrt{K} \left(n + \frac{3}{2}\right), \quad n = 0, 1, 2, \dots$$

Degeneracy:

even n	$l = 0, 2, \dots, n,$	$m = -l, -l + 1, \dots, 0, \dots, l - 1, l$	Bzero: $\frac{n+2}{2}$
odd n	$l = 1, 3, \dots, n,$	$m = -l, -l + 1, \dots, 0, \dots, l - 1, l$	Bzero: $\frac{n+1}{2}$

Operators commuting with Hamiltonian:

$$\hat{A}_{xx} - \hat{A}_{yy}, \quad \hat{A}_{yy} - \hat{A}_{zz}, \quad \hat{A}_{xz} + \hat{A}_{zx}, \quad \hat{A}_{yz} + \hat{A}_{zy}, \quad \hat{A}_{xy} + \hat{A}_{yx}$$

$$\hat{A}_{ij} = \hat{p}_i \hat{p}_j + K x_i x_j, \quad i, j = x, y, z$$

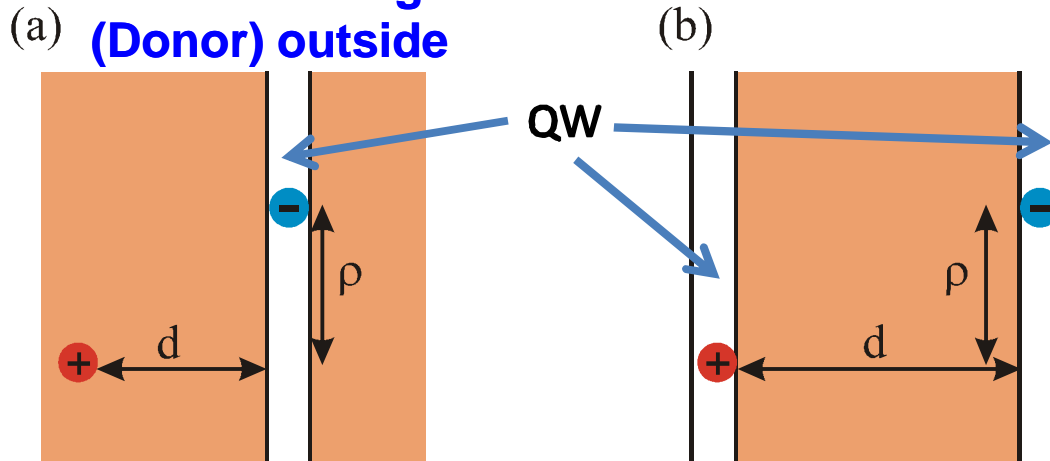
$$\hat{H} = \hat{A}_{xx} + \hat{A}_{yy} + \hat{A}_{zz}$$

2D Electron in Quantum Well Heterostructures

Electron inside QW and Positive Charge (Donor) outside

Spatially indirect exciton

Hamiltonian:



$$\hat{H} = -\Delta - \frac{2}{\sqrt{\rho^2 + d^2}}$$

$$Ry = \frac{m_e e^4}{2\epsilon^2 \hbar^2}$$

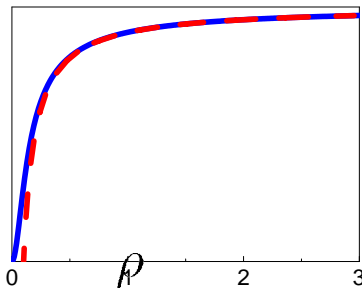
$$a_B = \frac{\hbar^2 \epsilon}{m_e e^2}$$

$d \rightarrow 0$

$d \rightarrow \infty$

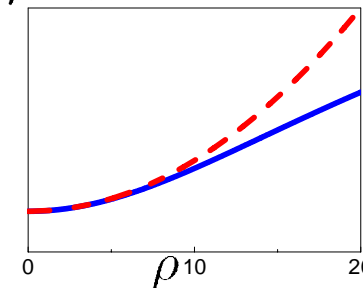
2D Hydrogen Atom

$$-\frac{2}{\sqrt{\rho^2 + d^2}} \approx -\frac{2}{\rho}$$

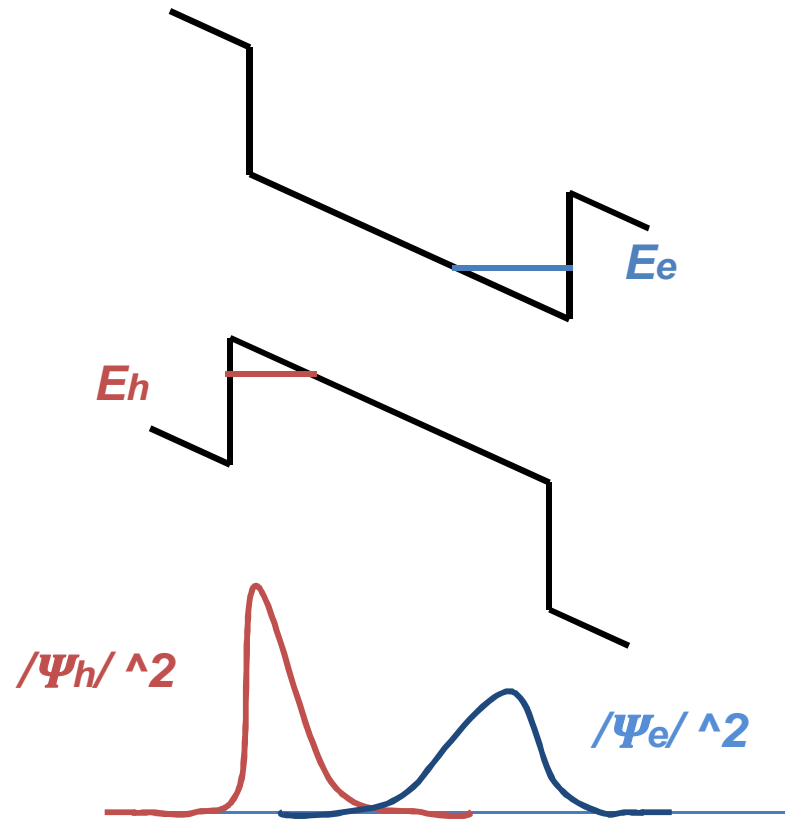
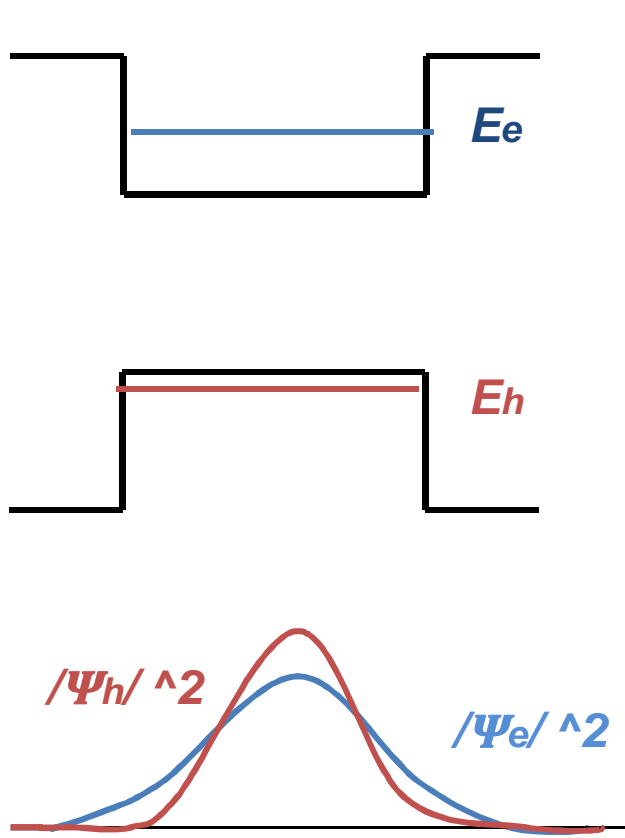


2D Isotropic Harmonic Oscillator

$$-\frac{2}{\sqrt{\rho^2 + d^2}} \approx -\frac{2}{d} + \frac{\rho^2}{d^3}$$



Field Control of Electron – Hole Interaction in Single Quantum Well



2D Hydrogen Atom

Hamiltonian:

$$\hat{H} = -\Delta - \frac{2}{\rho}$$

Energy Levels:

$$E_n = -\frac{1}{(n+1/2)^2}$$

Degeneracy:

$$m = -n, -n+1, \dots, n-1, n$$

total: $2n+1$

Wave Functions:

$$\psi_{nm}(\rho, \phi) = C_{n,m} \exp\left(-\frac{2\rho}{2n+1} - im\phi\right) \left(\frac{4\rho}{2n+1}\right)^{|m|} L_{n-|m|}^{2|m|}\left(\frac{4\rho}{2n+1}\right)$$

2D Laplace – Runge –Lentz Operator:

$$\hat{\mathbf{A}} = (\hat{\mathbf{p}} \times \hat{\mathbf{L}}_z - \hat{\mathbf{L}}_z \times \hat{\mathbf{p}}) - \frac{2}{\rho}\boldsymbol{\rho}$$

$$\hat{\mathbf{L}}_z = [\boldsymbol{\rho} \times \mathbf{p}]_z \mathbf{e}_z$$

2D Isotropic Harmonic Oscillator

Hamiltonian:

$$\hat{H} = -\Delta - \frac{2}{d} + \frac{\rho^2}{d^3}$$

Eigenenergies:

$$E_p = -\frac{2}{d} + \frac{2}{d^{3/2}}(p+1) \quad m = -p, -p+2, \dots, p-2, p$$

Degeneracy:

$$\text{total: } p+1$$

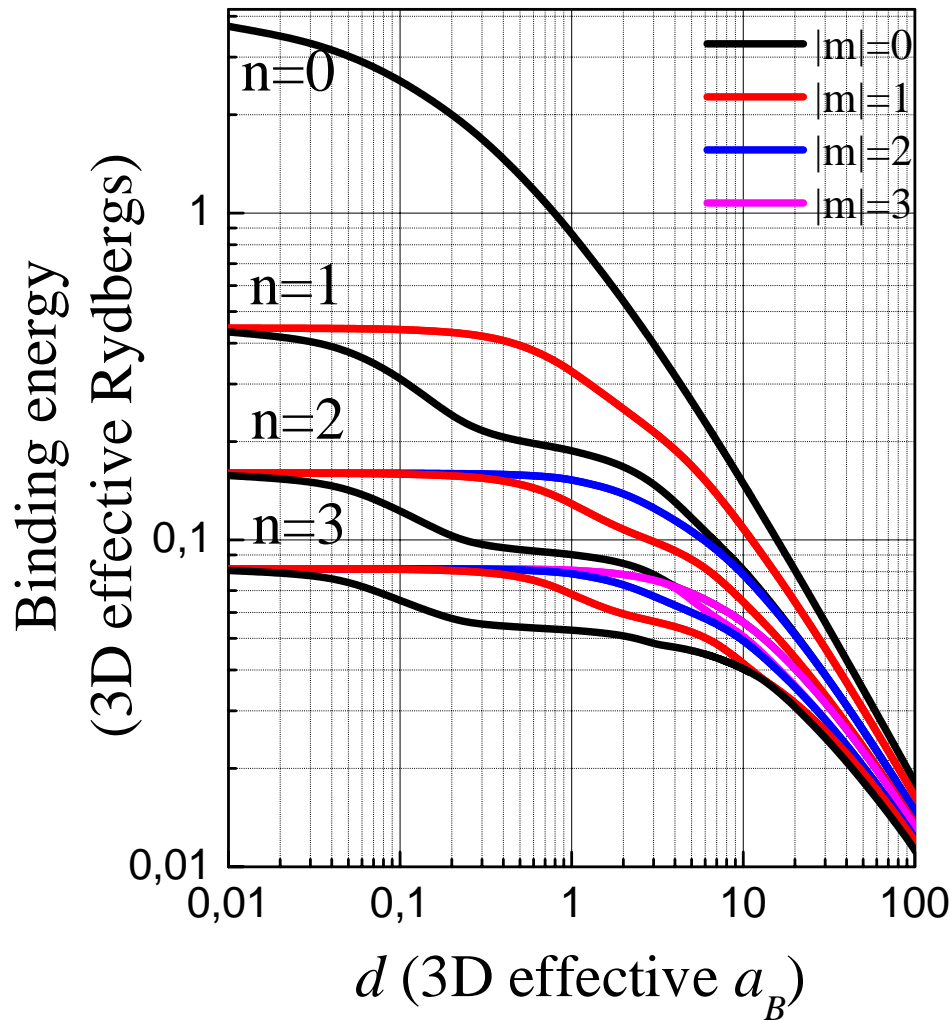
Eigenfunctions:

$$\psi_{pm}(\rho, \phi) = B_{p,m} \exp\left(-\frac{\rho^2}{2d^{3/2}} - im\phi\right) \left(\frac{\rho}{d^{3/2}}\right)^{|m|} L_{p/2-|m|/2}^{|m|}\left(\frac{\rho^2}{d^{3/2}}\right)$$

2 Component Operator commuting with Hamiltonian

$$S_x = p_x p_y + \frac{xy}{d^3}, \quad S_y = \frac{p_y^2 - p_x^2}{2} + \frac{y^2 - x^2}{2d^3}$$

Eigenenergies between Coulomb Potential and Harmonic Oscillator



Direct diagonalization

Basis @ $d < 20$

Hydrogen Atom Eigenfunctions Set

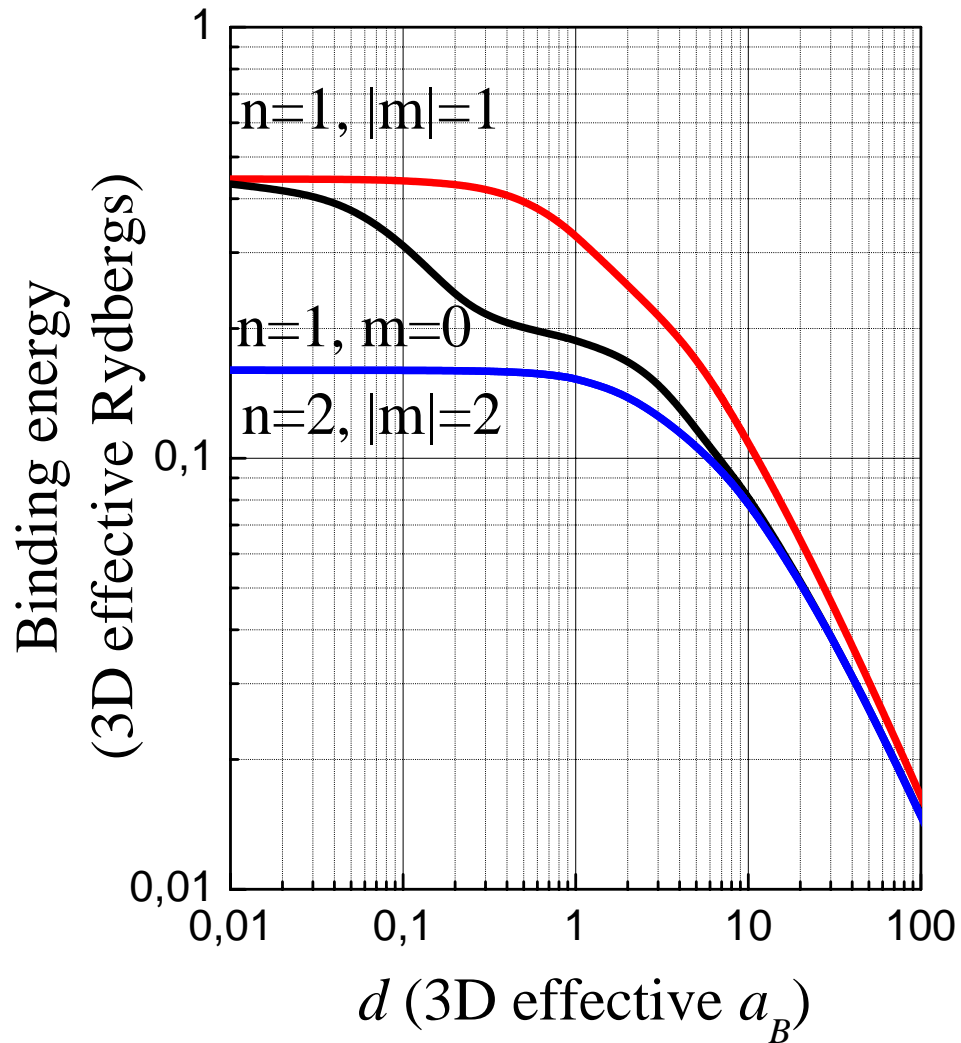
Basis @ $d > 100$

Oscillator Eigenfunctions Set

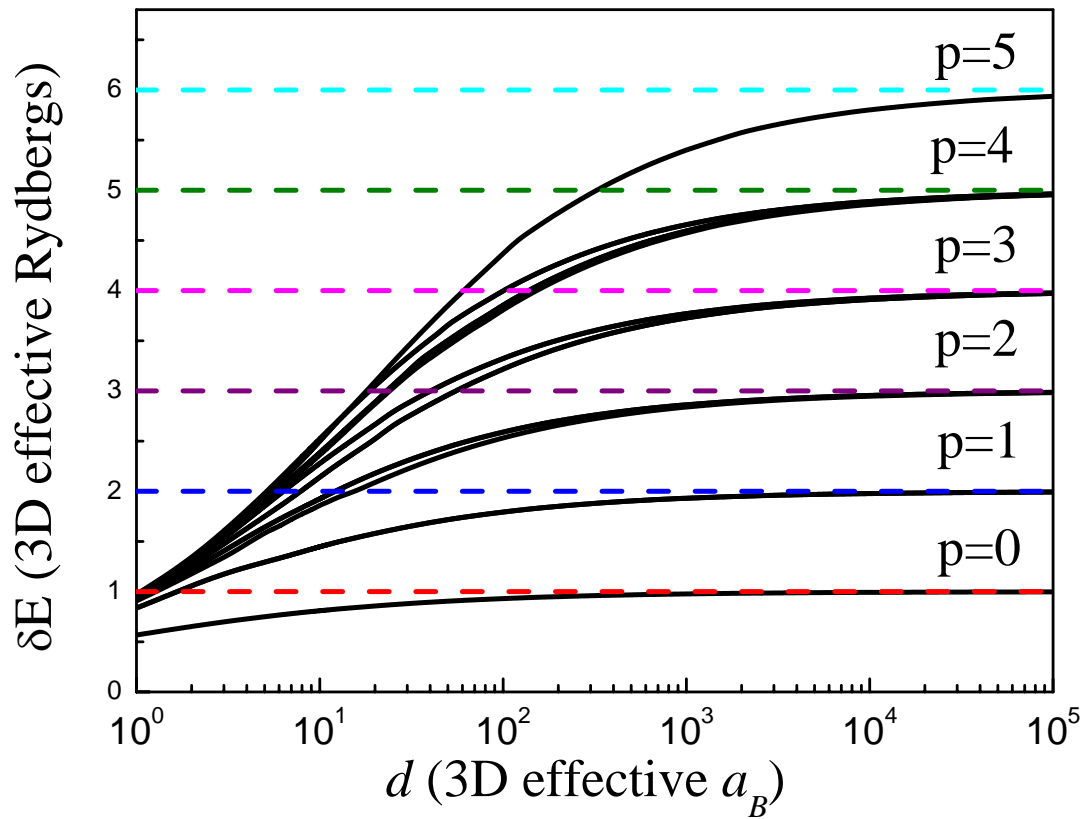
Basis @ $20 < d < 100$

Both Sets

Rearrangement of Energy Levels



Asymptotics of Energy Levels at $d \gg 1$



$$E_p = -\frac{2}{d} + \frac{2}{d^{3/2}}(p+1)$$

$$\delta E = \frac{1}{2} \left(E_p + \frac{2}{d} \right) d^{3/2}$$

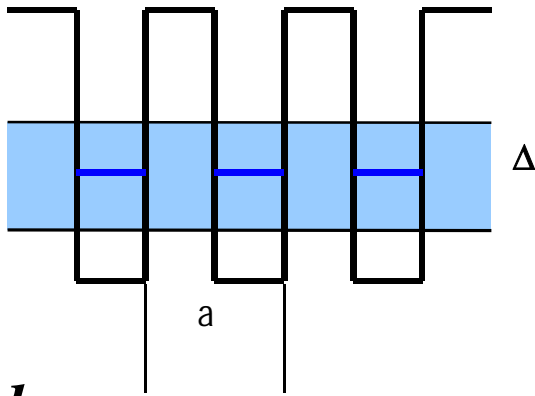
Conclusions to the Section 1

- ❖ **Semiconductor Quantum Well Nanostructures allow us to look after transition of eigenstates and eigenenergies between two systems with accidental degeneration**
- ❖ **In intermediate region, mixing of states with different principal quantum numbers becomes important in addition to the level splitting**
- ❖ **The region of applicability of both limiting case approximations depends on the eigenenergy, i.e., on the typical size of the corresponding eigenfunction**

Section 2.

Electron in Periodic Potential under Action of Constant Electric Field and Bloch Oscillations

Bloch oscillations: semi-classical description

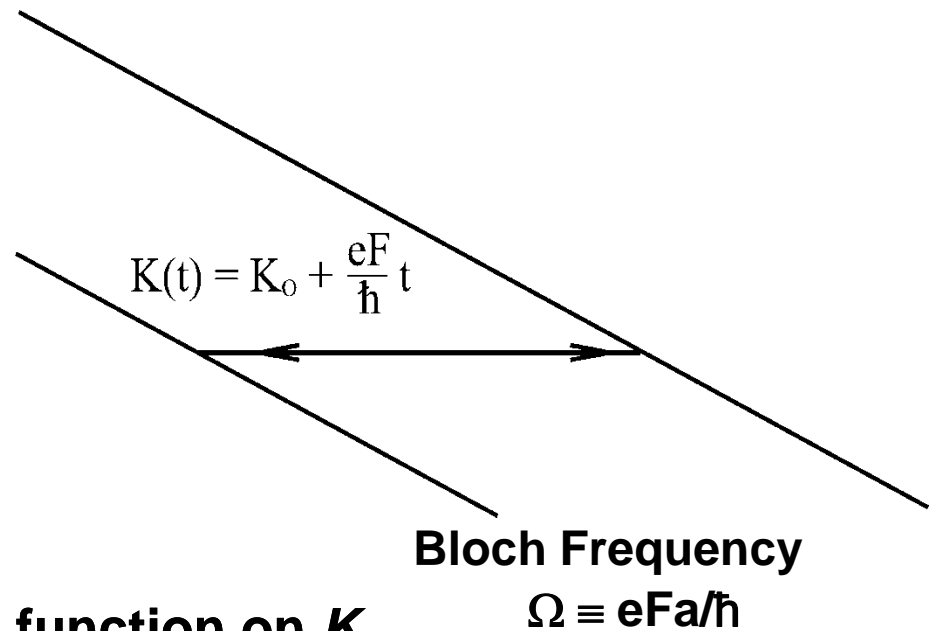


$$\frac{d}{dt} \hbar K = eF$$

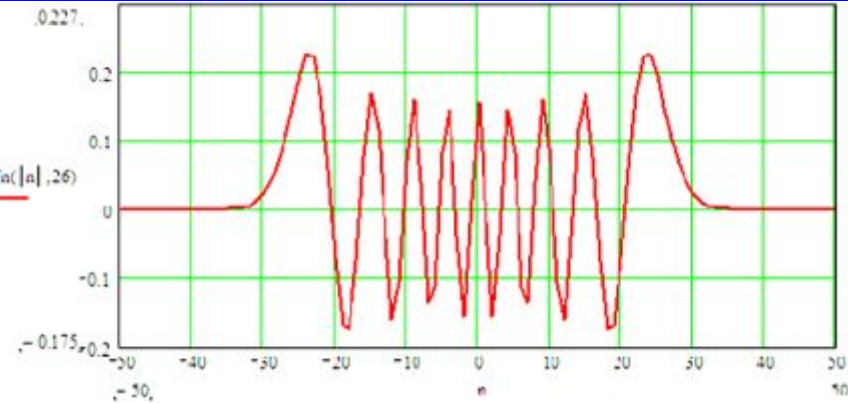
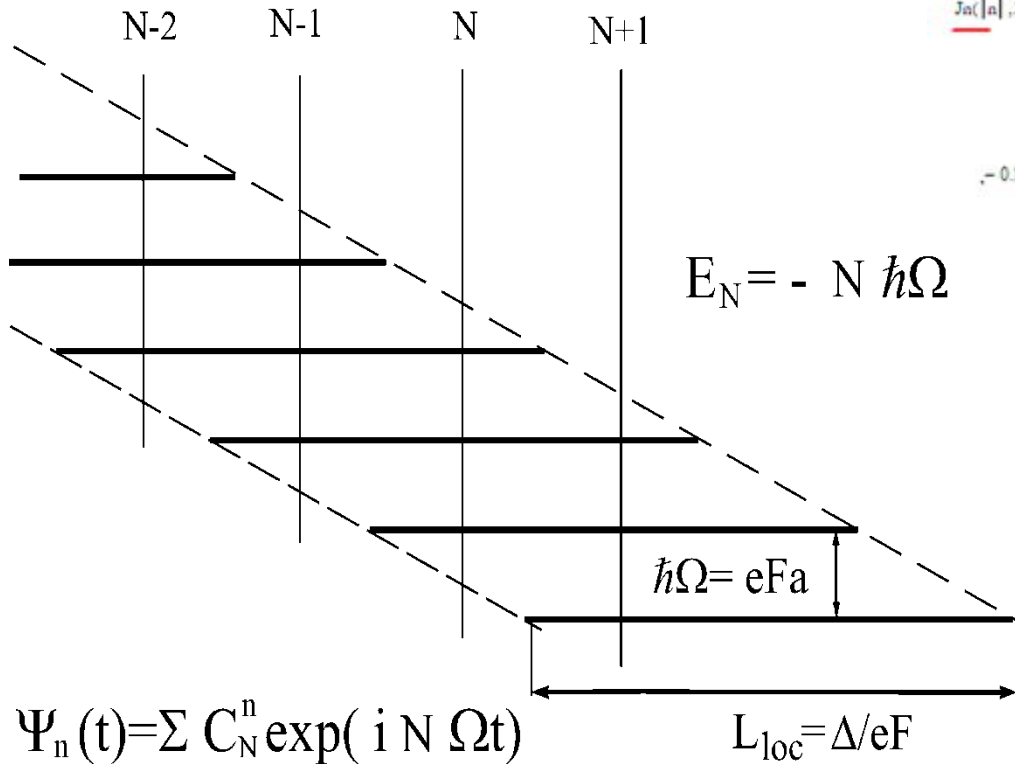
$$= K(0) + \frac{e}{\hbar} F t$$

$$v(t) = \left. \frac{\partial}{\partial K} E(K) \right|_{K(t)}$$

$E(K)$ – periodic function on K
It is why an electron oscillates relative some spatial position with Bloch frequency



Wannier-Stark Ladder



BO – Quantum Beating

Where Bloch Oscillations can be observed?

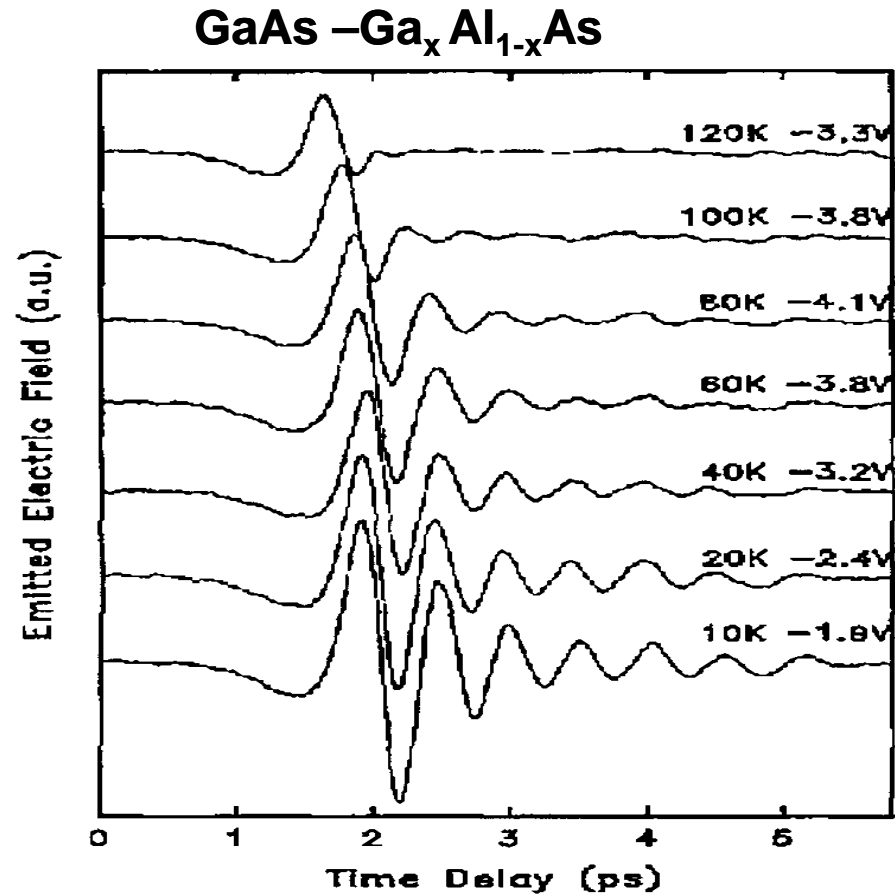
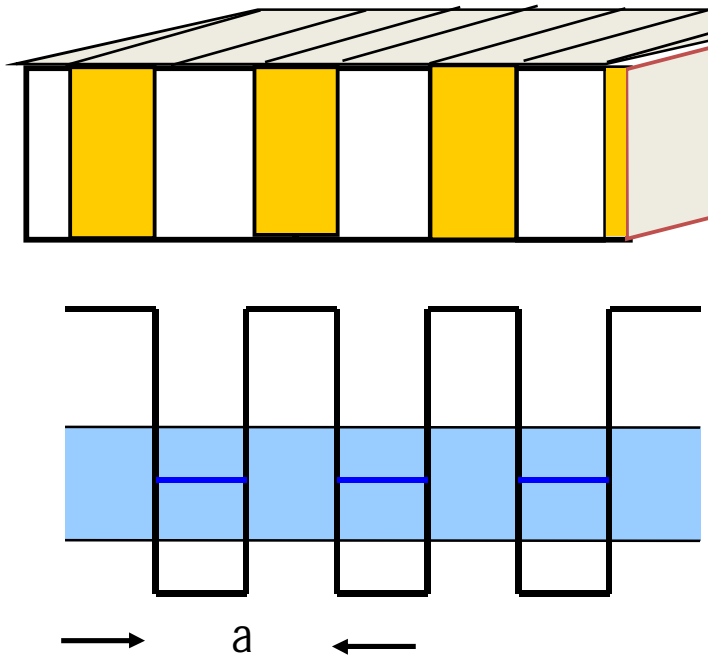
In natural crystals it is impossible to realize BO. It would require too strong electric field at which electric breakdown should occur.

However, it is possible in artificial crystals: semiconductor superlattices with lattice period strongly exceeding period of natural crystals (Man-made in contrast to God –made crystal: L. Esaki)

Very promising properties of the layered superlattices were described by V.A.Yakovlev (1961) and L.V. Keldysh (1962)

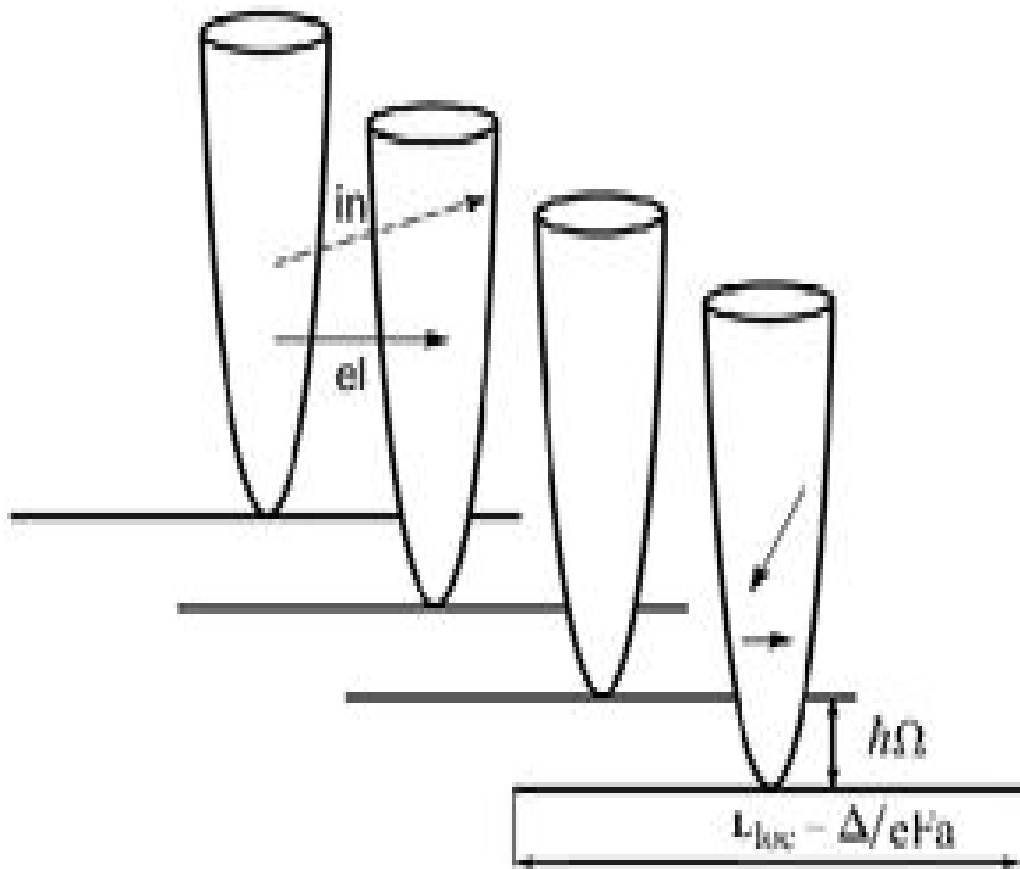
Artificial Layered Superlattice

The SL structures are fabricated with MBE or MOCVD technologies



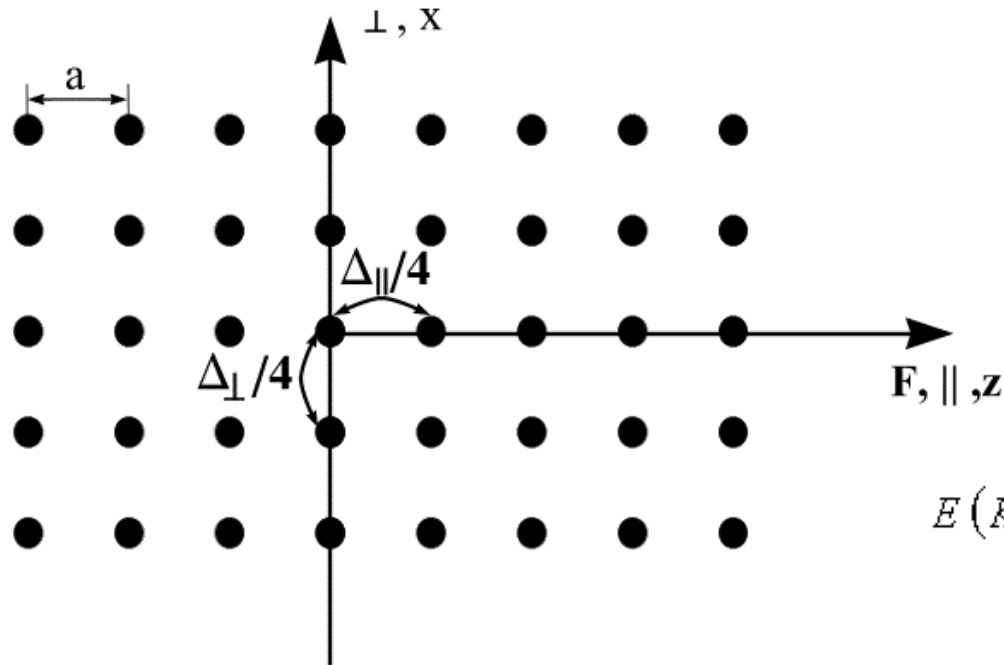
C.Waschke, H.G.Roskos, K Leo, H. Kurz, K.Köhler, *Semicond. Sci.Technol.*, 9, 416, 1994.

Scattering Processes Layered Superlattice



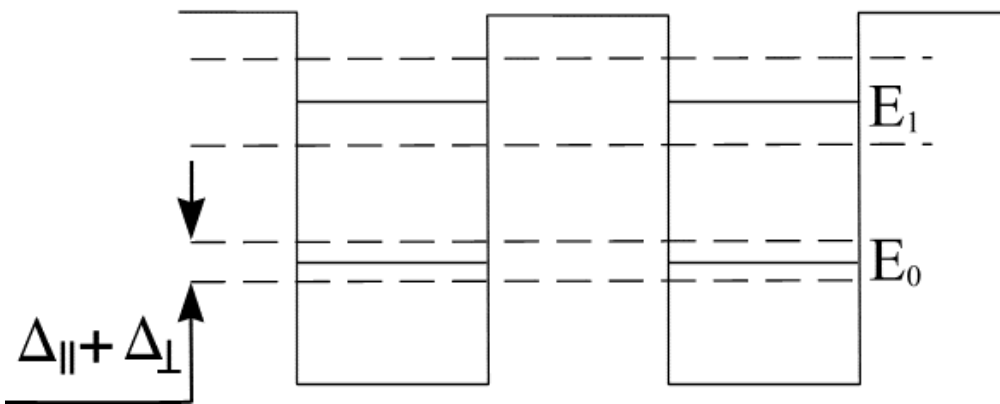
$$E_N(k_{\perp}) = -eFN + \frac{\hbar^2 k_{\perp}^2}{2m}$$

Quantum Dot Superlattice



$$E(K) = \frac{\Delta_{\perp}}{2} \cos(k_{\perp} a) + \frac{\Delta_{\parallel}}{2} \cos(k_{\parallel} a)$$

$$\Delta_{\perp} + \Delta_{\parallel} \ll |E_0 - E_1|$$



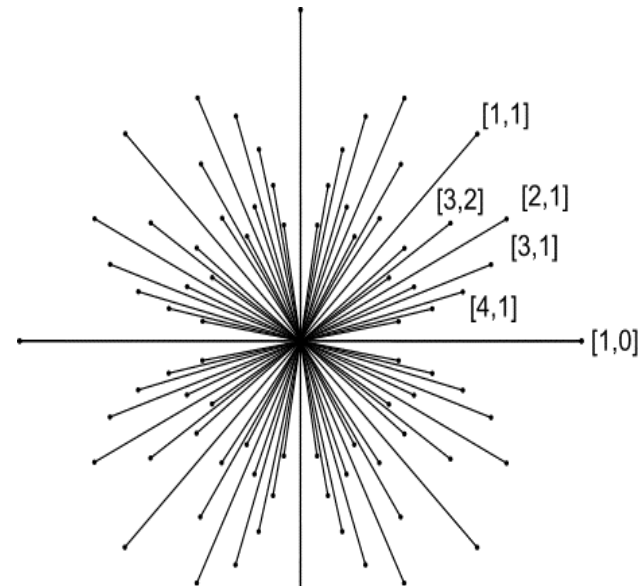
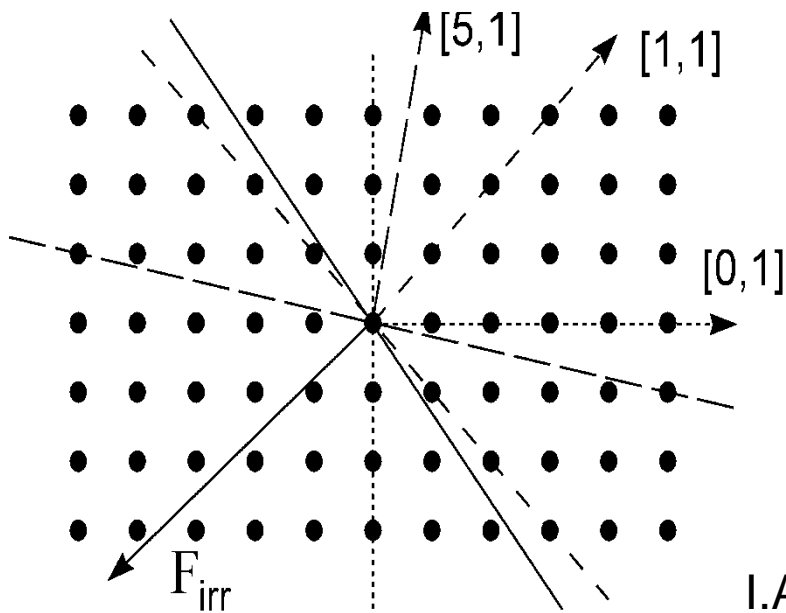
Exponential dependence of transverse minibands width in QDSL

$$E_{\mathbf{R}}(\mathbf{k}) = -e\mathbf{F} \cdot \mathbf{R} + \sum_{\rho} \frac{\Delta_{\rho}}{4} (1 - \cos(\mathbf{k}\boldsymbol{\rho}))$$

Rational Electric Field Direction

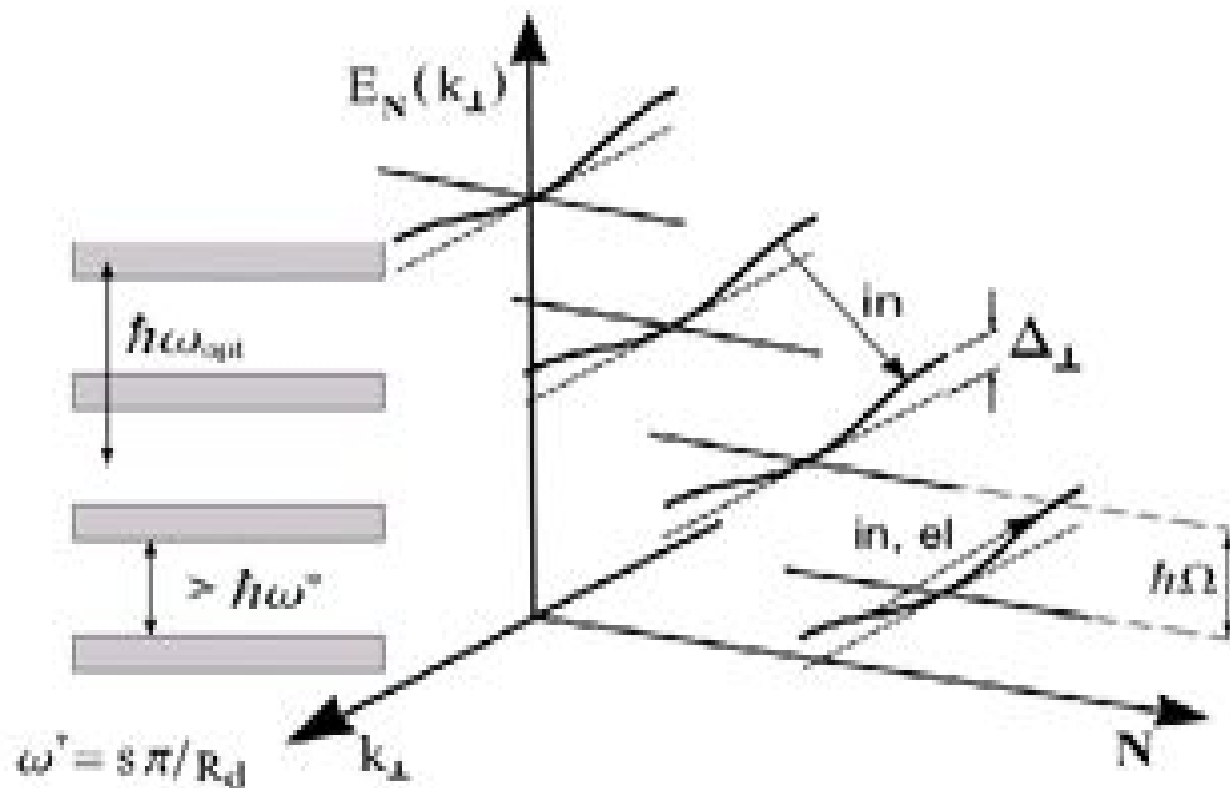
$$E_{\mathbf{R}}(\mathbf{k}) = -e\mathbf{F} \cdot \mathbf{R} = -\sum n_i \hbar \Omega_i$$

Irrational Electric Field Direction

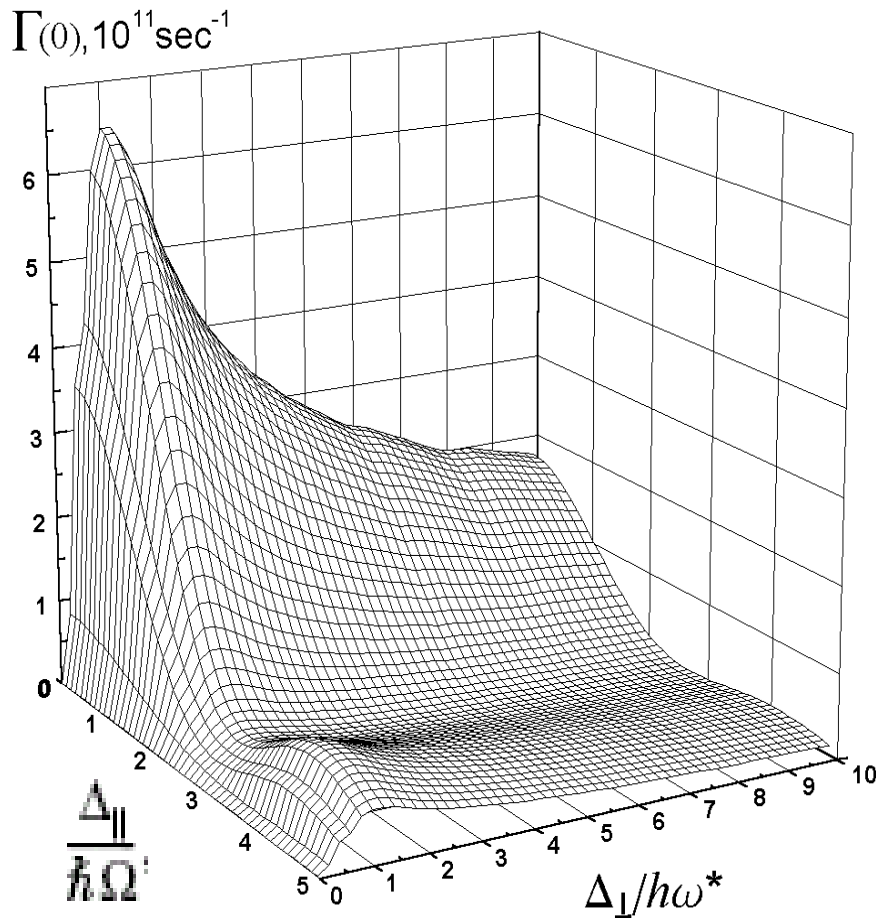


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Scattering Suppression in Quantum Dot Superlattice



BO damping rate as a function of localization length and transverse miniband width



QDSL with Period $a = 100 \text{ \AA}$

QD size $R_D = 25 \text{ \AA}$,

$\hbar\omega^* = \hbar s \pi / R_D = 4.3 \text{ meV}$ –

actual acoustic phonon energy.

Conclusions to the Section 2

- ◆ QDSL application enables us to control the scattering processes. It results in a profound extent of the BO lifetime.
Varying the electric field value and orientation in QDSL allows us to:
 - qualitatively change the spectrum of electrons, from the continuous one to the purely discrete one;
 - control the transverse miniband width in a wide range since it *exponentially* depends on the field orientation;
 - totally suppress the optical phonon scattering which is the main mechanism of scattering in QWSL;
 - make negligibly small the acoustic phonon scattering between transverse minibands;
 - strongly reduce the intraminiband acoustic phonon scattering by choosing appropriate electric field strength and miniband width.
- ◆ BO damping rate at T=300 K $\gamma \propto 10^{13} \text{ sec}^{-1}$ in QWSL $\gamma \propto 10^{10} \text{ sec}^{-1}$ in QDSL
- ◆ The BO in QDSL are a superposition of 2 (2D SL) or 3 (3D SL) oscillations with frequencies proportional to the field projections on the principal SL axis's.